Amendments to the Specification:

Please amend the paragraph beginning at page 3, line 16 of the specification as follows:

As described above, according to the conventional method of correcting a clear defect in an HT mask (i.e., a clear defect on a substrate of an HT mask), the clear defect is corrected by the deposition of a carbon film about which the phase effect cannot be used for any defect correction portion, the carbon film having a transmissivity of about 0% to an exposure wavelength. Therefore, the working accuracy tolerance margin of the correction portion becomes small, which .—Thus, there is caused a problem that a causes an error of in the size and shape of a device pattern transferred on a wafer (the error resulting from the location accuracy, the edge shape and the skirt-trailing of the carbon film formed on the photomask). The error negatively impacts produces a seriously bad effect on the performance of the semiconductor device.

Please amend the paragraph beginning at page 4, line 27 of the specification as follows:

As a result, in the case that where the photomask, wherein with its clear defect portion is corrected by the semitransparent portion, is used to transfer a pattern corresponding to the clear defect portion onto a semiconductor substrate, the rate of occurring a occurrence of dimensional fluctuation of the transferred pattern on the semiconductor substrate can be made small. Accordingly, the yield of semiconductor devices can be improved.

Please amend the paragraph beginning at page 10, line 18 of the specification as follows:

When a relationship between the correction offset of carbon film 3 on a transparent substrate 100 and the dimensional fluctuation coefficient of the pattern on a wafer is estimated by optical intensity simulation, a relationship as shown in Fig. 2 is obtained. The dimensional fuluctuation fluctuation coefficient is defined as the ratio of the dimension of a pattern

transferred on a wafer to that of an imaginary pattern. Conditions for the simulation are as follows: wavelength: 248 nm; numerical aperture (NA) of the exposure apparatus: 0.68; transmissivity of wiring pattern 1 as the semitransparent film: 6%; transmissivity of carbon film 3: 0%; and defect size: 0.52 μm x 0.8 μm.

Please amend the Abstract of the Disclosure on page 47 of the specification as follows:

A shading area having a transmissivity in the range of 0 to 2% is formed at the center of a clear defect in a wiring pattern of a ~~halt~~ half tone mask. Semitransparent areas having a transmissivity in the range of 10 to 25% are formed, adjacently to shading area, in areas extending from the inside of the edge of an imaginary pattern having no defect to the outside of the edge. In this way, in the correction of the defect in the half tone mask, the working accuracy tolerable margin of the correction portion of the defect can be made large.